

INN100EBD035DAD-C

1. General Description

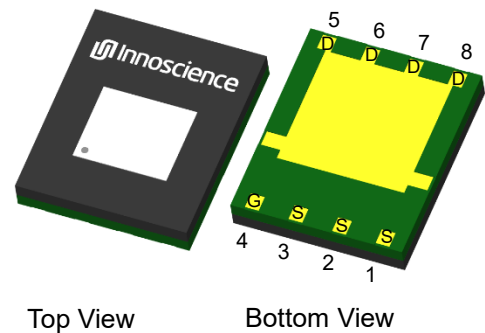
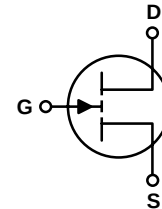
GaN-on-Silicon enhancement mode high-electron-mobility-transistor (HEMT) in En-FCLGA with 5.0 mm x 6.0 mm package size.

2. Features

- GaN-on-Silicon E-mode HEMT technology
- Industry application
- Very low gate charge
- Ultra-low on resistance
- Very small footprint

3. Applications

- High frequency DC-DC converter
- High density DC/DC power module
- Synchronous rectification
- Motor driver
- Solar system MPPT



4. Key Performance Parameters

Table 1 Key performance parameters at $T_J = 25\text{ }^{\circ}\text{C}$

Parameter	Value	Unit
$V_{DS,max}$	100	V
$R_{DS(on),typ} @ V_{GS} = 5\text{ V}$	2.9	$m\Omega$
$R_{DS(on),max} @ V_{GS} = 5\text{ V}$	3.5	$m\Omega$
$Q_{G,typ} @ V_{DS} = 50\text{ V}$	7.7	nC
$I_{DS,Pulse} (T_J = 25\text{ }^{\circ}\text{C})$	390	A
$Q_{OSS} @ V_{DS} = 50\text{ V}$	41	nC

5. Pin Information

Table 2 Pin information

PIN	Pin Description	Pin Function
1,2,3	Source	Power Source
5-8	Drain	Power Drain
4	Gate	Driver Gate

Table 3 Ordering information

Type/Ordering Code	Package	Product Code
INN100EBD035DAD	En-FCLGA 5.0 x 6.0	J52

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6. Maximum Ratings

at $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Exceeding the maximum ratings may destroy the device. For further information, contact Innoscence sales office.

Table 4 Maximum ratings

SYMBOL	PARAMETER	MAX	UNIT
V_{DS}	Drain-to-Source Voltage	100	V
$V_{DS(tr)}$	Drain-to-Source Voltage ¹ ($V_{GS} = 0\text{ V}$, 1h total time, $T_A = T_{JMAX}$)	120	V
I_D	Continuous current ($V_{GS} = 5\text{ V}$, $T_C = 25\text{ }^{\circ}\text{C}$, $R_{\theta JC} = 0.5\text{ }^{\circ}\text{C/W}$)	187	A
	Continuous current ($V_{GS} = 5\text{ V}$, $T_C = 100\text{ }^{\circ}\text{C}$, $R_{\theta JC} = 0.5\text{ }^{\circ}\text{C/W}$)	118	A
	Continuous current ($V_{GS} = 5\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, $R_{\theta JA} = 41.4\text{ }^{\circ}\text{C/W}$)	20	A
	Pulsed ($V_{GS} = 5\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$, $T_{Pulse} = 100\text{ }\mu\text{s}$)	390	A
	Pulsed ($V_{GS} = 5\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$, $T_{Pulse} = 100\text{ }\mu\text{s}$)	300	A
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	V
$V_{GS(tr)}$	Gate-to-Source Voltage ¹ ($V_{DS} = 0\text{ V}$, 168h total time, $T_A = T_{JMAX}$)	6.5	V
P_{tot}	Power dissipation ($V_{GS} = 5\text{ V}$, $T_C = 25\text{ }^{\circ}\text{C}$, $R_{\theta JC} = 0.5\text{ }^{\circ}\text{C/W}$)	255	W
	Power dissipation ($V_{GS} = 5\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, $R_{\theta JA} = 41.4\text{ }^{\circ}\text{C/W}$)	2.9	W
T_J	Operating Temperature	-40 to 150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-55 to 150	$^{\circ}\text{C}$

Note:

1. Provided as measure of robustness under abnormal operating conditions and not recommended for normal operation;

7. Thermal Characteristics

Table 5 Thermal characteristics

SYMBOL	PARAMETER	TYP	UNIT	Note/Test Condition
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.5	°C/W	-
$R_{\theta JB}$	Thermal Resistance, Junction to Board	4.5	°C/W	-
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ²	41.4	°C/W	-
T_{sold}	Maximum reflow soldering temperature	260	°C	MSL3

Note:

- $R_{\theta JA}$ is determined with the device on FR4 PCB (2s2p with thermal vias) defined in accordance with JEDEC standards. PCB is mounted in horizontal position without air stream cooling.

8. Electric Characteristics

at $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 6 Static characteristics

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITIONS
I_{DSS}	Drain Source Leakage	-	1	100	μA	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$
	Drain Source Leakage ($T_J = 125\text{ }^{\circ}\text{C}$)	-	200	-	μA	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$
I_{GSS}	Gate-to-Source Forward Leakage	-	0.5	100	μA	$V_{GS} = 6\text{ V}$
	Gate-to-Source Forward Leakage ($T_J = 125\text{ }^{\circ}\text{C}$)		50	-	μA	$V_{GS} = 6\text{ V}$
	Gate-to-Source Reverse Leakage	-	0.1	100	μA	$V_{GS} = -4\text{ V}$
$V_{GS(TH)}$	Gate Threshold Voltage ³	0.8	1.1	2.1	V	$V_{DS} = V_{GS}$, $I_D = 7.6\text{ mA}$
$R_{DS(on)}$	Drain-Source On-state Resistance ³	-	2.9	3.5	$\text{m}\Omega$	$V_{GS} = 5\text{ V}$, $I_D = 2.5\text{ A}$
V_{SD}	Source-Drain Forward Voltage	-	1.8	-	V	$I_S = 25\text{ A}$, $V_{GS} = 0\text{ V}$

Note:

3. $V_{GS(TH)}$ and $R_{DS(on)}$ is measured without prior drain bias or switching stress.

Table 7 **Dynamic characteristics** ⁴

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITIONS
C _{ISS}	Input Capacitance	-	950	-	pF	V _{GS} = 0 V, V _{DS} = 50 V
C _{OSS}	Output Capacitance	-	430	-		V _{GS} = 0 V, V _{DS} = 50 V
C _{RSS}	Reverse Transfer Capacitance	-	7	-		V _{GS} = 0 V, V _{DS} = 50 V
C _{OSS(ER)}	Energy Related C _{OSS}	-	590	-		V _{GS} = 0 V, V _{DS} = 0 V to 50 V
C _{OSS(TR)}	Time Related C _{OSS}	-	830	-		V _{GS} = 0 V, V _{DS} = 0 V to 50 V
R _G	Gate Resistance	-	1.6	-	Ω	f = 5 MHz, open drain
Q _G	Total Gate Charge	-	7.7	-	nC	V _{GS} = 5 V, V _{DS} = 0 V to 50 V, I _D = 25 A
Q _{GS}	Gate to Source Charge	-	1.7	-		V _{GS} = 5 V, V _{DS} = 0 V to 50 V, I _D = 25 A
Q _{GD}	Gate to Drain Charge	-	1.2	-		V _{GS} = 5 V, V _{DS} = 0 V to 50 V, I _D = 25 A
V _{Plat}	Gate Plateau Voltage	-	1.8	-	V	I _D = 25A, V _{DS} = 50V, V _{GS} = 0V to 5V
Q _{G(TH)}	Gate Charge at Threshold	-	1	-	nC	V _{GS} = 5 V, V _{DS} = 0 V to 50 V, I _D = 25 A
Q _{OSS}	Output Charge	-	41	-		V _{GS} = 0 V, V _{DS} = 0 V to 50 V
Q _{RR}	Reverse Recovery Charge	-	0	-		V _{DS} = 50 V, I _S = 25 A

Note:

4. Guaranteed by design.

9. Electric Characteristics Diagrams

at $T_J = 25\text{ }^{\circ}\text{C}$, unless specified otherwise

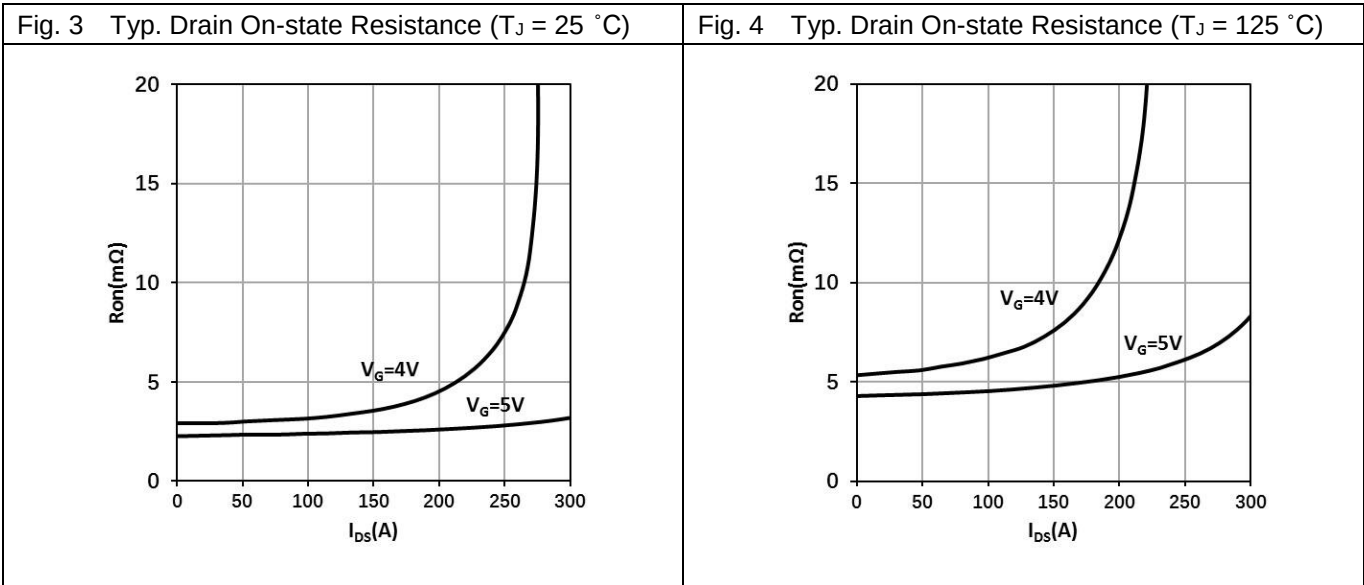
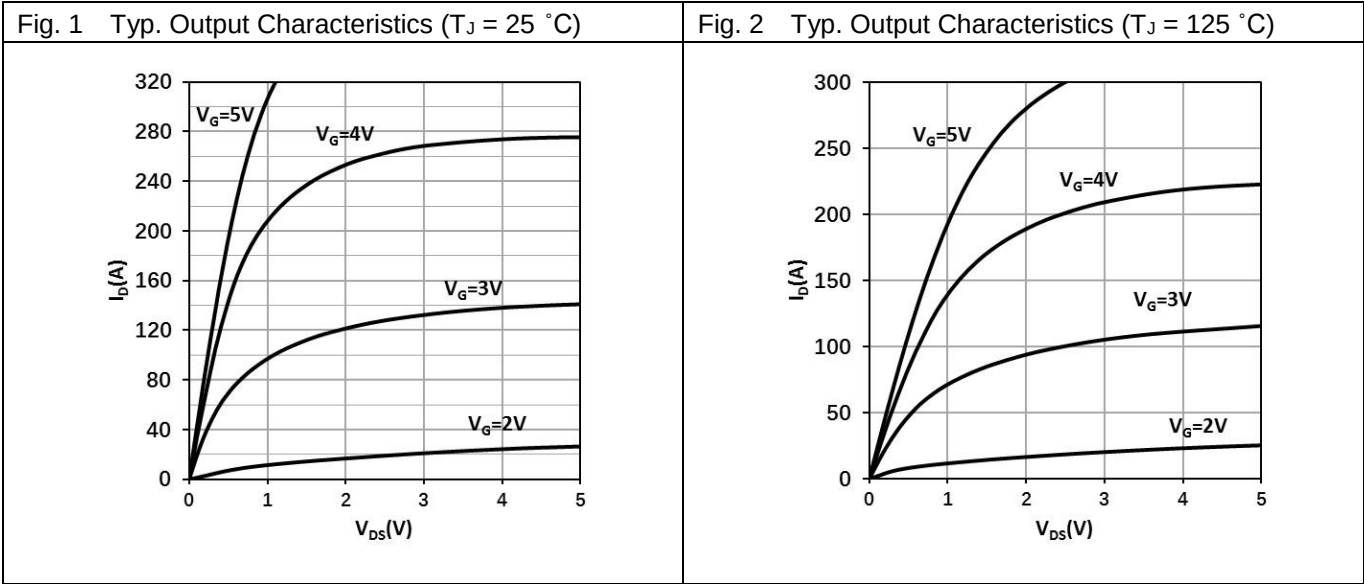


Fig. 5 Normalized On-State Resistance vs. Temp.

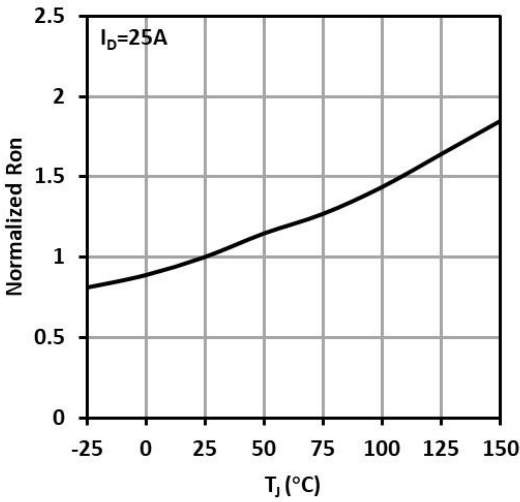


Fig. 6 Typ. Transfer Characteristics

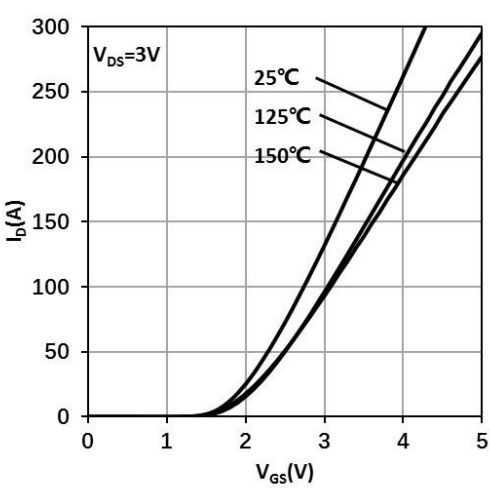


Fig. 7 Typ. Reverse Drain-Source Characteristics ($V_{GS} \leq 0$, $T_J = 25^\circ C$)

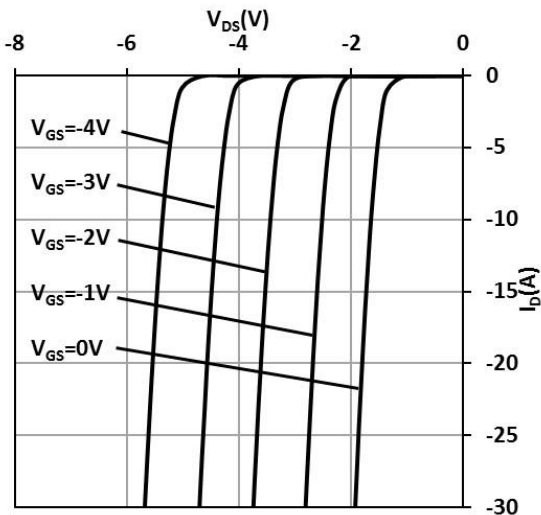


Fig. 8 Typ. Reverse Drain-Source Characteristics ($V_{GS} \geq 0$, $T_J = 25^\circ C$)

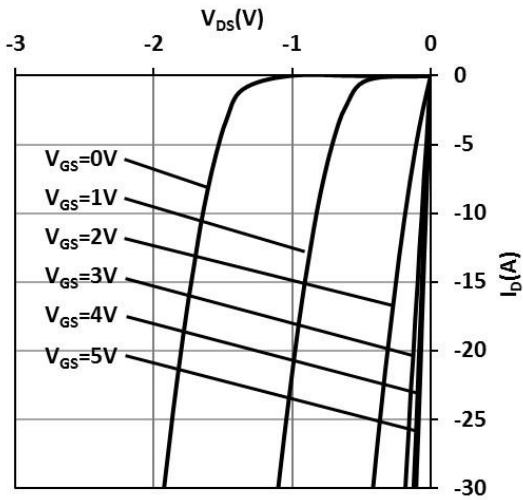


Fig. 9 Typ. Reverse Drain-Source Characteristics
($V_{GS} \leq 0$, $T_J = 125^\circ\text{C}$)

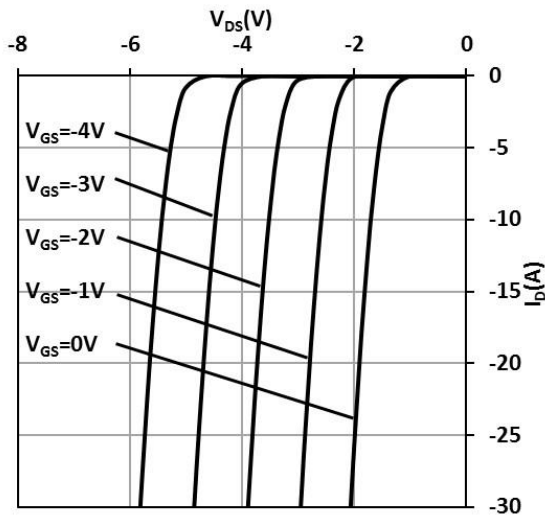


Fig. 10 Typ. Reverse Drain-Source Characteristics
($V_{GS} \geq 0$, $T_J = 125^\circ\text{C}$)

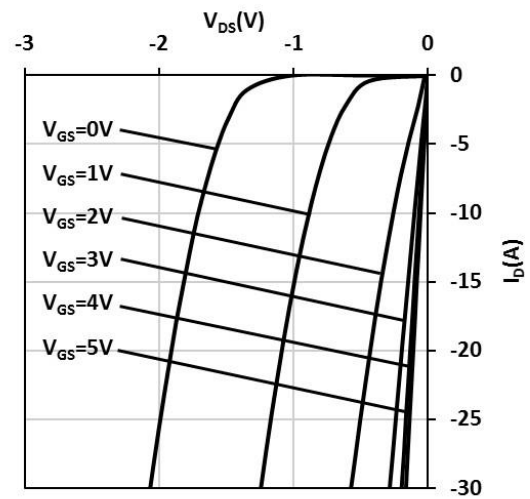


Fig. 11 Typ. Capacitances Characteristics

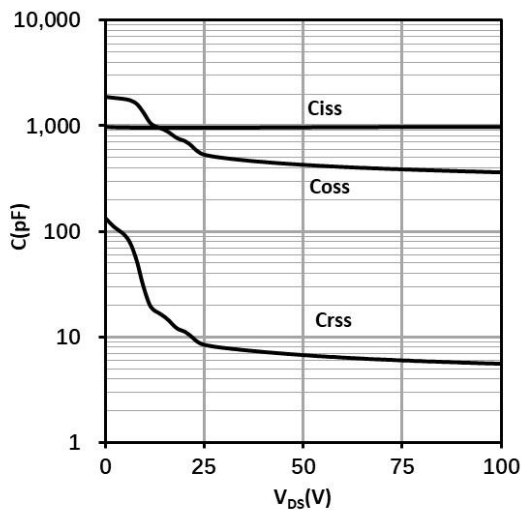


Fig. 12 Typ. Gate Charge

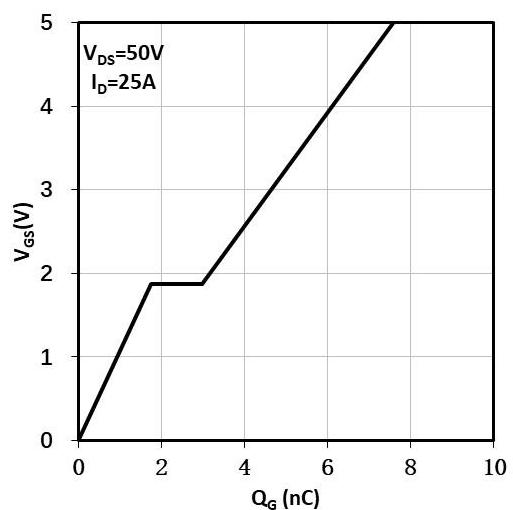


Fig. 13 Normalized Threshold Voltage vs. Temp.

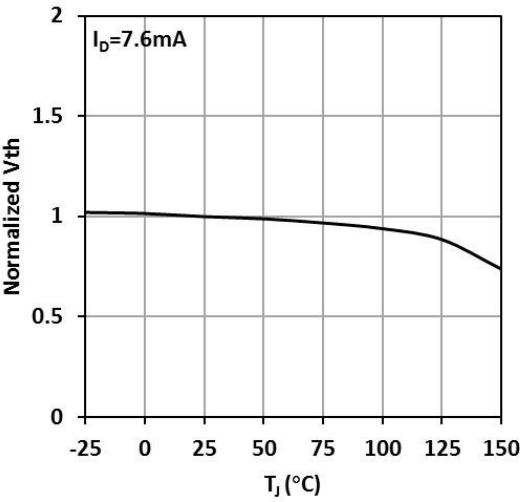


Fig. 14 Typ. Output Charge

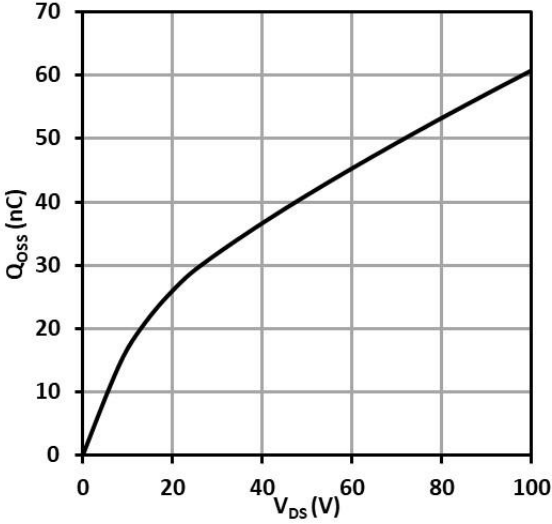


Fig. 15 Typ. Output Capacitance Stored Energy

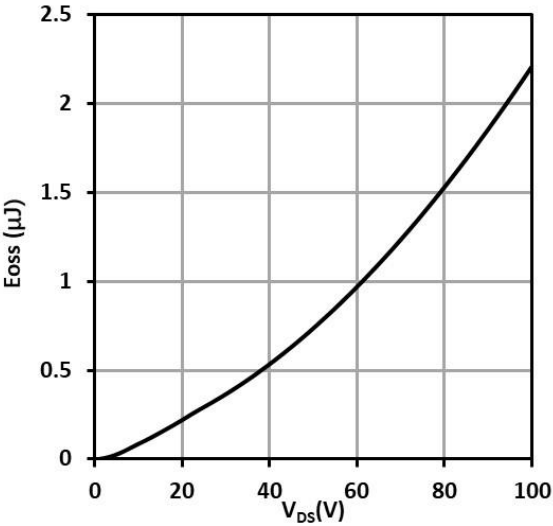


Fig. 16 Power Dissipation $P_{tot} = f(T_c)$, $R_{\theta JC} = 0.5\text{ }^{\circ}\text{C/W}$

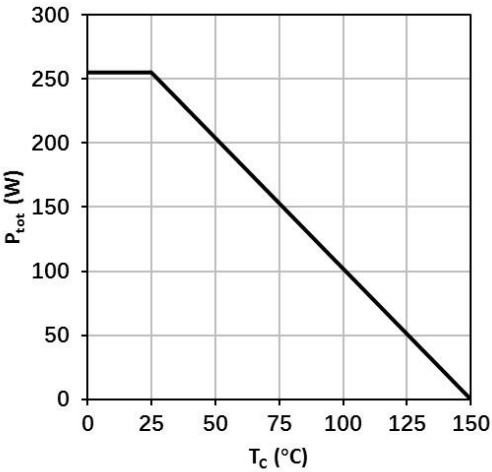


Fig. 17 Power Dissipation $P_{tot} = f(T_A)$, $R_{\theta JA} = 41.4^\circ\text{C/W}$

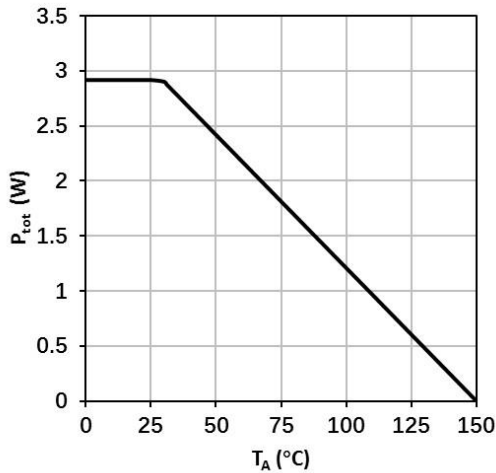


Fig. 18 Typ. Gate-to-Source Leakage Characteristics $I_G = f(V_{GS})$; Drain Open

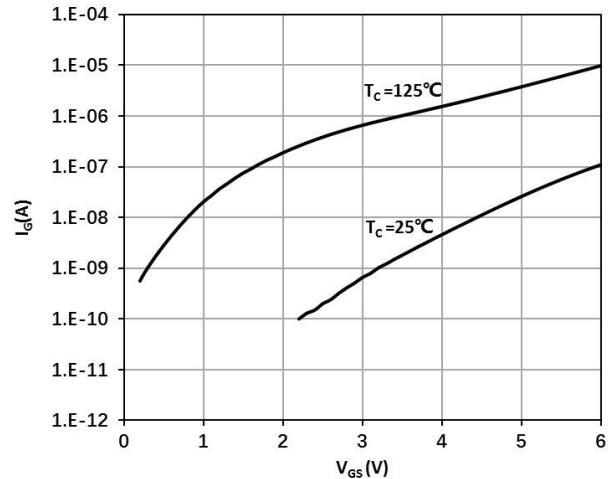


Fig. 19 Typ. Drain-Source Leakage Characteristics $I_{DSS} = f(V_{DS})$; $V_{GS} = 0\text{ V}$

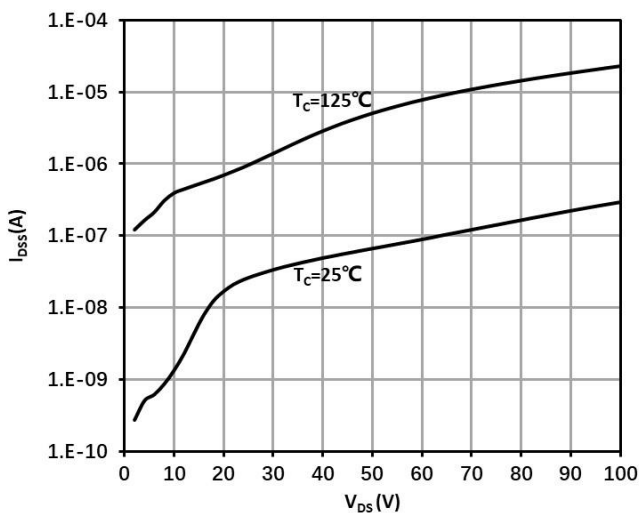


Fig. 20 Safe Operating Area $I_D = f(V_{DS})$; $T_c = 25^\circ\text{C}$; Single Pulse; Parameter: t_p

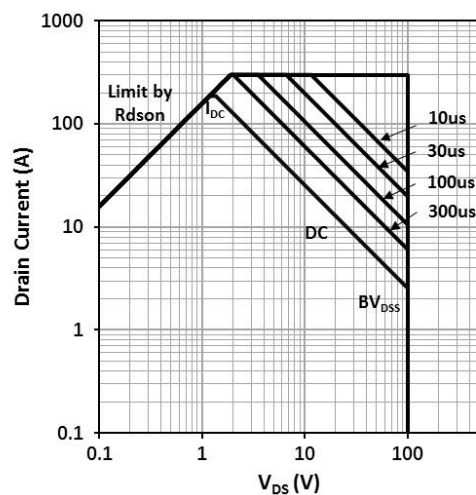


Fig. 21 Safe Operating Area
 $I_D = f(V_{DS})$; $T_C=125^{\circ}\text{C}$; Single Pulse; Parameter: t_p

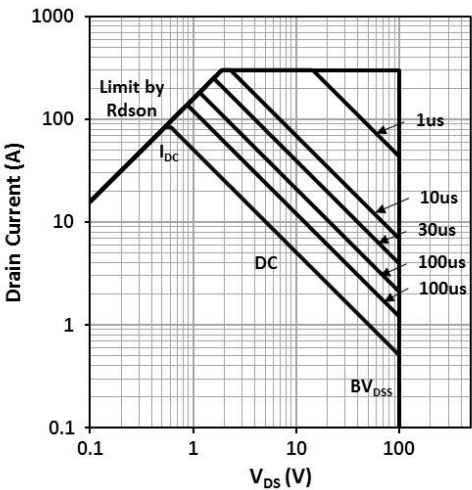
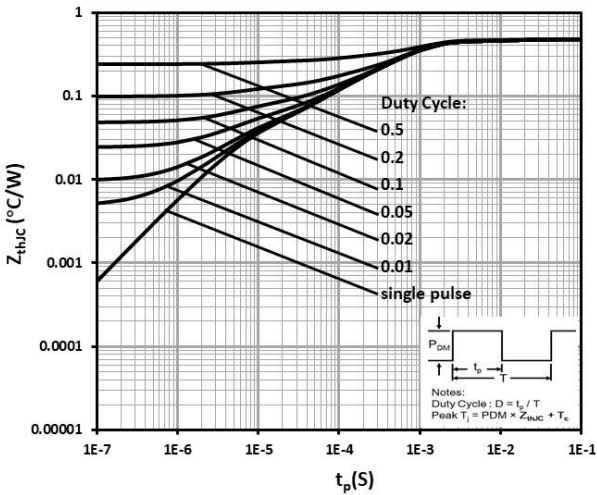
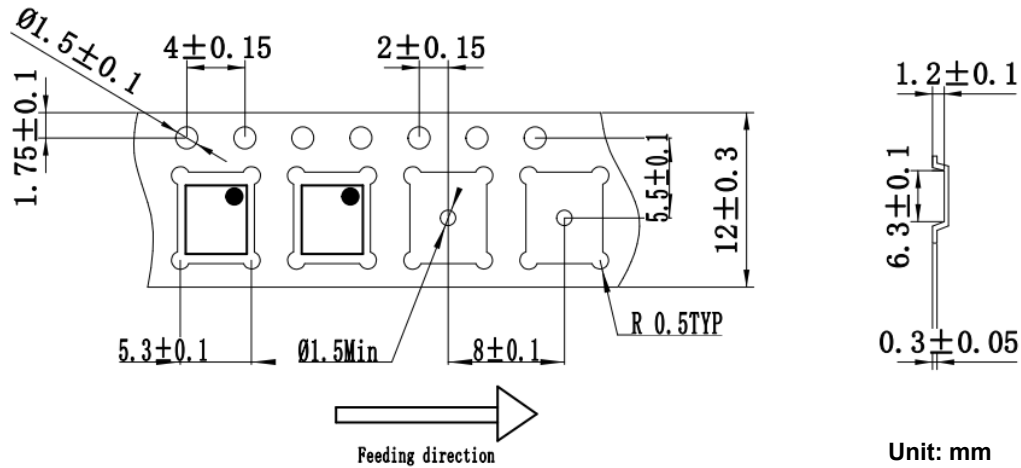


Fig. 22 Max. Transient Thermal Impedance
 $Z_{thJC} = f(t_p)$; Parameter: $D=t_p/T$

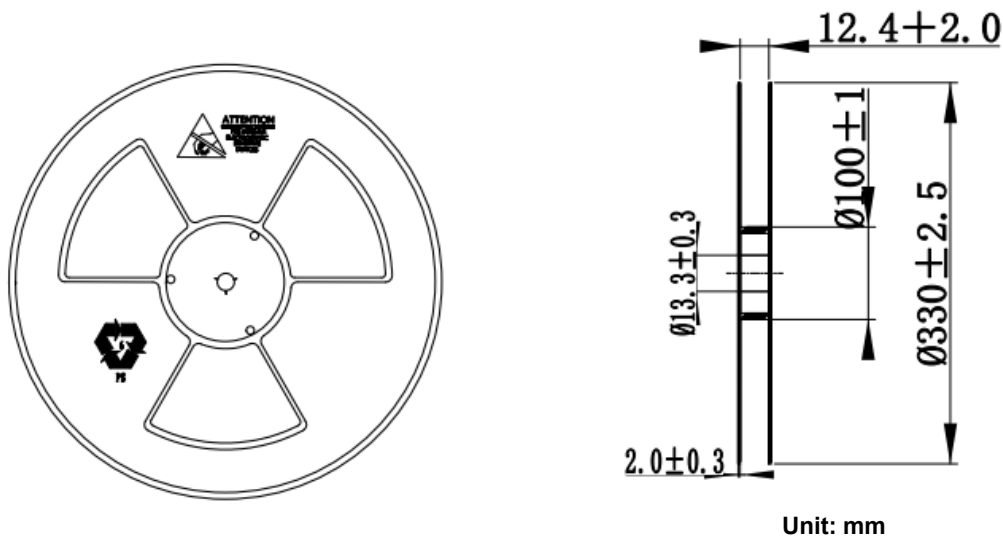


11. Reel Information



Notes:

- (1) The cumulative error of any 10 sprocket holes shall not exceed $\pm 0.20\text{mm}$;
- (2) The material thickness shall be measured based on the edge of the carrier tape;
- (3) The unspecified tolerance is $\pm 0.1\text{mm}$, and $R < 0.3\text{mm}$ is not specified;
- (4) The unmarked demolding slope is 5° ;
- (5) Surface Resistivity: $1 \times 10^5 \Omega/\Delta \sim 1 \times 10^9 \Omega/\Delta$

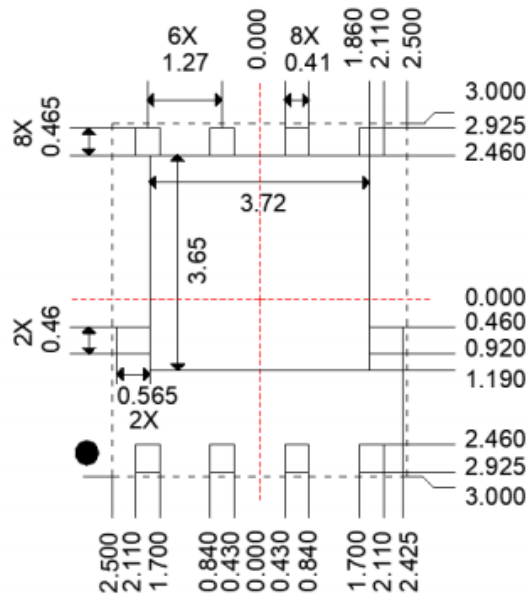


Notes:

1. The surface of the product should be smooth, clean, and free of injection molding defects, and there should be no significant burrs;
2. Material surface resistance: $1 \times 10^5 \Omega/\Delta \sim 1 \times 10^9 \Omega/\Delta$;
3. No tolerance marked: $\pm 0.3\text{mm}$;

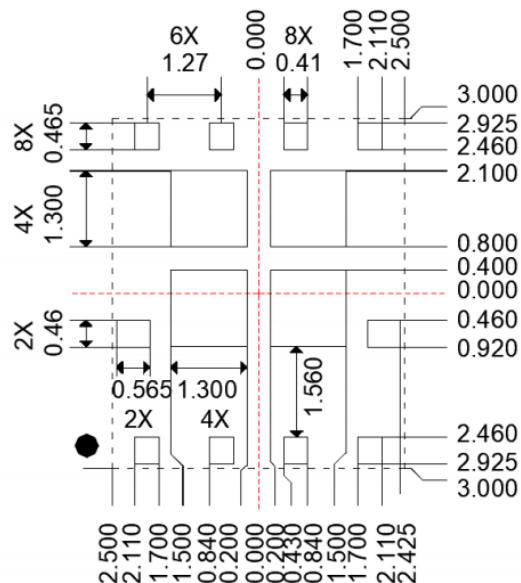
12. Land Pattern

Recommended Land Pattern



Unit: mm

Recommended Stencil Drawing



Unit: mm

13. Revision History

Major changes since the last revision

Revision	Date	Description of changes
1.0	2025-07-10	1.0 version setup
1.1	2025-08-06	1. Update I_{GSS} Typ. in Table 6 2. Correct Fig.18 and Fig.19 in Electric Characteristics Diagrams 3. Correct typos in Marking reference

Important Notice

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